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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/045,542	10/26/2001	Mrinal Kanti Das	5308-157IP2	3570	
20792	7590 11/21/2002				
MYERS BIGEL SIBLEY & SAJOVEC			EXAMINER		
PO BOX 374:	·· -	BARR, MICHAEL E			
RALEIGH, N	C 27627		Dride, Micliab L		
	•		ART UNIT	PAPER NUMBER	
			1762	5	
			DATE MAILED: 11/21/2002	-	

Please find below and/or attached an Office communication concerning this application or proceeding.

•			Ω 1
	Application No.	Applicant(s)	7
	10/045,542	DAS ET AL.	
Office Action Summary	Examiner	Art Unit	
	Michael Barr	1762	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with	the correspondence addr	ess
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	136(a). In no event, however, may a rep ly within the statutory minimum of thirty (will apply and will expire SIX (6) MONTH e, cause the application to become ABAI	ly be timely filed 30) days will be considered timely. IS from the mailing date of this comi NDONED (35 U.S.C. § 133).	munication.
1) Responsive to communication(s) filed on	·		
2a) This action is FINAL . 2b) ⊠ Th	nis action is non-final.		
3) Since this application is in condition for allows closed in accordance with the practice under Disposition of Claims			merits is
4)⊠ Claim(s) <u>1-20</u> is/are pending in the application	n.		
4a) Of the above claim(s) is/are withdra	wn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-20</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/o	or election requirement.		
Application Papers			
9) The specification is objected to by the Examine	<u> </u>	. F	
10) ☐ The drawing(s) filed on is/are: a) ☐ acce			
Applicant may not request that any objection to th 11) The proposed drawing correction filed on	* '	, ,	
If approved, corrected drawings are required in re		approved by the Examiner.	
12) The oath or declaration is objected to by the Ex	. •		
Priority under 35 U.S.C. §§ 119 and 120			
13) Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C. &	119(a)-(d) or (f)	
a) ☐ All b) ☐ Some * c) ☐ None of:	in priority and or or o.o. o.	, , , (a) (a) (i).	
1.☐ Certified copies of the priority document	s have been received.		
2.☐ Certified copies of the priority document		olication No.	
3. Copies of the certified copies of the prio application from the International Bu * See the attached detailed Office action for a list	rity documents have been re reau (PCT Rule 17.2(a)).	eceived in this National St	age
14)⊠ Acknowledgment is made of a claim for domesti			pplication).
a) ☐ The translation of the foreign language pro 15)☑ Acknowledgment is made of a claim for domest	* *		
Attachment(s)		_	
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 2	5) Notice of Inf	mmary (PTO-413) Paper No(s). ormal Patent Application (PTO-	

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DETAILED ACTION

Claim Rejections - 35 USC § 112

- 1. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 2. Claims 8, 13, and 16 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 8 cites the limitation of heating "as a part of another processing step". It is not clear in the claim as to what is meant by "another processing step". Another with respect to what?

Claim 13 cites the limitation of "high temperature". "High" is a relative term which renders the claim vague and indefinite since there is no clear definition provided to show what temperatures are considered to be high.

Claim 16 cites the limitation of "a contact anneal". It is not clear as to what is meant by a "contact anneal". Does this merely refer to the hydrogen contacting the substrate during the anneal? The examiner is prosecuting the claim with this interpretation.

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are

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such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 1-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over JP 2000-252461 by Arai et al. ("Arai") in view of the article by Xu et al. ("Xu").

Arai teaches making a MOS semiconductor device where a silicon carbide layer, on a non-SiC surface, is provided with a gate oxide or nitride layer on its surface, which is then annealed in a hydrogen atmosphere at 600-1600°C for 10 seconds-3 hours, where the hydrogen atmosphere can be a mixture of hydrogen gas and inert gas with the mixture being 05.5-100% hydrogen, where the SiC can be a 4H polytype SiC (Paragraphs 003, 006-008, 0016-0018). Arai teaches that the MOS device can be on a printed circuit (Paragraph 001).

Arai does not teach that the oxide or nitride layer is a nitrided oxide layer. However, the teaching of Arai that the layer can be an oxide or nitride on the SiC would have suggested to one skilled in the art that a mixture of the two would have also provided suitable results in the device of Arai. Xu teaches making a MOS semiconductor device, similar to that of Arai, wherein a silicon carbide layer is provided with an oxide layer on its surface, where a nitrided oxide layer is preferred over an oxide layer, since the nitrided layer improves the interface qualities of the oxide layer with the SiC, as opposed to the oxide layer alone, where the layer can be applied by forming an oxide layer and then nitriding/annealing with N₂O, or by oxidizing in pure N₂O and then further annealing (see Introduction and Experiments sections). It would have been an obvious modification to Arai to provide a nitrided oxide layer on the SiC of the MOS semiconductor device in the manner taught by Xu, in order to improve the interface density with the SiC, as is taught by Xu and since it is taught by Arai that both oxide and nitride layers are

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used in the process, which would have suggested to one skilled in the art that a mixture of the two would have also provided suitable results in the device of Arai.

Arai and Xu do not teach annealing with hydrogen concurrently with the nitriding process. However, the performance of two steps simultaneously, which have previously been performed in sequence, is considered to be obvious (*In re Tatincloux* 108 USPQ 125). Therefore, it is the examiner's position that the performance of the hydrogen annealing and nitriding, in Arai and Xu, simultaneously would have been an obvious modification, with the expectation of providing the desired nitriding and annealing results.

With regards to Claim 13, these limitations merely read on typical semiconductor device use in an air environment, which contains hydrogen.

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Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael Barr whose telephone number is 703-305-7919. The examiner can normally be reached on Monday-Thursday 6:00 am-4:30 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Shrive Beck can be reached on 703-308-2333. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9310 or 703-305-5408 for regular communications and 703-872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0661.

Michael Barr Primary Examiner Art Unit 1762

MB

November 12, 2002